

### 2STW4466

### High power NPN epitaxial planar bipolar transistor

#### **Features**

- High breakdown voltage V<sub>CEO</sub> = 80V
- Complementary to 2STW1693
- Typical f<sub>t</sub> = 20MHz
- Fully characterized at 150 °C

## **Applications**

Audio power amplifier

#### **Description**

The device is a NPN transistor manufactured in low voltage planar technology using base island layout. The resulting transistor shows good gain linearity coupled with low V<sub>CESAT</sub> behaviour. Recommended for 45W to 70W high fidelity audio frequency amplifier output stage.

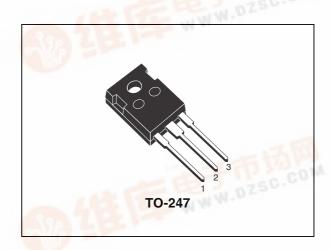


Figure 1. Internal schematic diagram

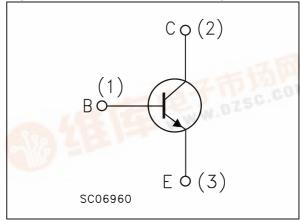


Table 1. Device summary

Order code	Marking	Package	Packaging
2STW4466	2STW4466	TO-247	Tube
<b>西维库</b>	WWW.DZSC.COM		

## **Contents**

1	Elec	trical ratings	3
2	Elec	trical characteristics	4
	2.1	Electrical characteristics (curves)	.5
3	Pack	kage mechanical data	7
4	Revi	sion history	g

2STW4466 Electrical ratings

## 1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-emitter voltage (I <sub>E</sub> = 0)	100	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	80	V
V <sub>EBO</sub>	Collector-base voltage (I <sub>C</sub> = 0)	6	V
Ic	Collector current	6	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5ms)	12	Α
P <sub>TOT</sub>	Total dissipation at T <sub>c</sub> = 25°C	60	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-amb</sub>	Thermal resistance junction-amb max	2.08	°C/W

Electrical characteristics 2STW4466

### 2 Electrical characteristics

 $(T_{CASE} = 25^{\circ}C; unless otherwise specified)$ 

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 100V			0.1	μА
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 6V			0.1	μА
V <sub>(BR)EBO</sub>	Collector-emitter breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 1mA	6			V
V <sub>(BR)CBO</sub>	Collector-emitter breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = 100μA	100			V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 50mA	80			V
V <sub>CE(sat)</sub> (1)	Concotor crimitor cataration	$I_C = 2A$ $I_B = 200 \text{mA}$ $I_C = 6A$ $I_B = 600 \text{mA}$			0.6 1.5	V V
V <sub>BE</sub> (1)	Base-emitter voltage	$V_{CE} = 5V$ $I_{C} = 5A$			1.5	V
h <sub>FE</sub>	DC current gain	$I_C = 2A$ $V_{CE} = 4V$	50		120	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> = 0.5A V <sub>CE</sub> = 12V		20		MHz
C <sub>CBO</sub>	Collector-base capacitance	I <sub>E</sub> = 0 V <sub>CB</sub> = 10V f = 1MHz		50		pF
t <sub>on</sub>	Turn-on time	$I_C = 3A$ $V_{CC} = 30V$		0.15		ns
t <sub>stg</sub>	Storage time	$I_{B1} = -I_{B2} = 0.3A$		1.5		ns
t <sub>off</sub>	Fall time	ואין – ואין – ואין		0.1		ns

*Note:* 1 Pulsed duration = 300  $\mu$ s, duty cycle  $\leq$ 1.5%

**2STW4466** Electrical characteristics

#### 2.1 Electrical characteristics (curves)

Figure 2. DC current gain

Figure 3. DC current gain

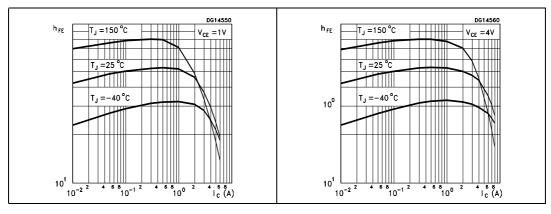


Figure 4. Collector-emitter saturation voltage

Figure 5. Base-emitter saturation voltage

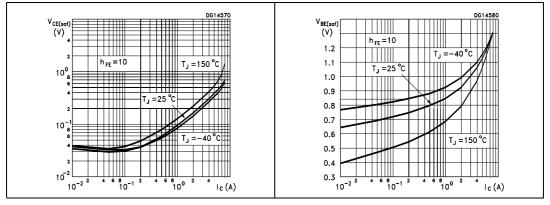
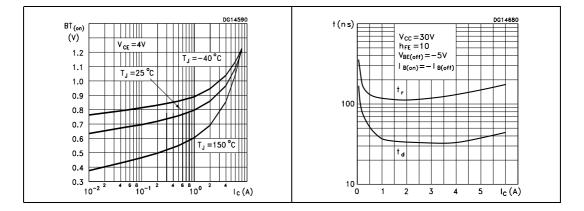


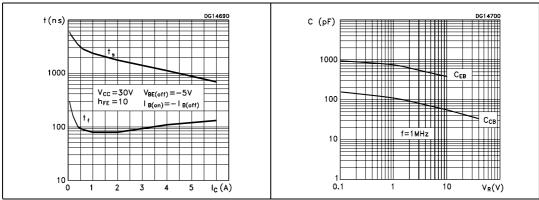
Figure 6. BT<sub>(ON)</sub> time

Figure 7. Resistive load switching time



Electrical characteristics 2STW4466

Figure 8. Switching time resistive load Figure 9. Collector-base and collector-emitter capacitance



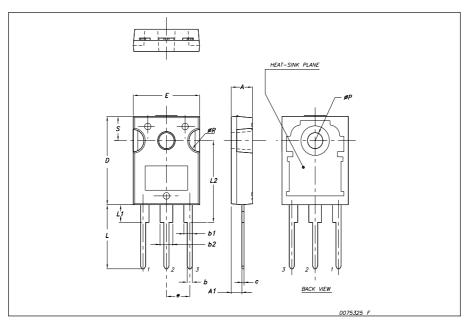
# 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



#### **TO-247 Mechanical data**

Dim.	mm.		
Dilli.	Min.	Тур	Max.
Α	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
С	0.40		0.80
D	19.85		20.15
E	15.45		15.75
е		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øΡ	3.55		3.65
øR	4.50		5.50
S		5.50	



2STW4466 Revision history

## 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
11-Oct-2007	1	First release

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57